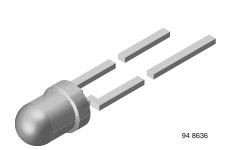
**GREEN** 

(5-2008)\*\*



### Vishay Semiconductors

# High Power Infrared Emitting Diode, 940 nm, GaAlAs/GaAs



#### **DESCRIPTION**

TSAL4400 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

#### **FEATURES**

Package type: leadedPackage form: T-1

• Dimensions (in mm): Ø 3

Peak wavelength: λ<sub>p</sub> = 940 nm

High reliability

• High radiant power

High radiant intensity

• Angle of half intensity:  $\varphi = \pm 25^{\circ}$ 

Low forward voltage

Suitable for high pulse current operation

• Good spectral matching with Si photodetectors

Package matches with detector TEFT4300

 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### Note

\*\* Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

#### **APPLICATIONS**

- · Infrared remote control units
- Free air transmission systems
- · Infrared source for optical counters and card readers

PRODUCT SUMMA	ARY			
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>P</sub> (nm)	t <sub>r</sub> (ns)
TSAL4400	30	± 25	940	800

#### Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATI	ON		
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL4400	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

#### Note

· MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1.5	Α	
Power dissipation		P <sub>V</sub>	160	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	t ≤ 5 s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	300	K/W	





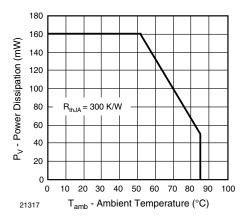


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

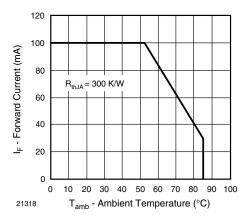


Fig. 2 - Forward Current Limit vs. Ambient Temperature

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	$V_{F}$		1.35	1.6	V
	$I_F = 1 \text{ A, } t_p = 100  \mu\text{s}$	$V_{F}$		2.6	3	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μΑ
Junction capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	C <sub>j</sub>		25		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	16	30	80	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	l <sub>e</sub>	135	240		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фe		35		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 20 mA	TKφ <sub>e</sub>		- 0.6		%/K
Angle of half intensity		φ		± 25		deg
Peak wavelength	I <sub>F</sub> = 100 mA	$\lambda_{p}$		940		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		50		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 100 mA	$TK\lambda_p$		0.2		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		800		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		800		ns
Virtual source diameter	Method: 63 % encircled energy	d		1.9		mm

# Vishay Semiconductors

### **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

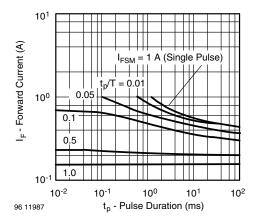


Fig. 3 - Pulse Forward Current vs. Pulse Duration

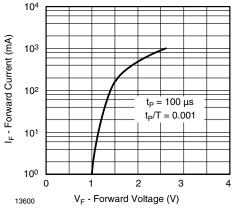


Fig. 4 - Forward Current vs. Forward Voltage

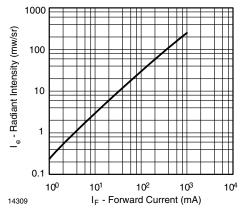


Fig. 5 - Radiant Intensity vs. Forward Current

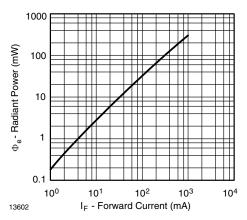


Fig. 6 - Radiant Power vs. Forward Current

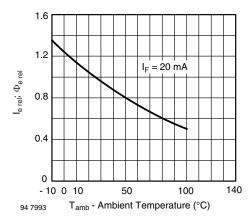


Fig. 7 - Rel. Radiant Intensity/Power vs. Ambient Temperature

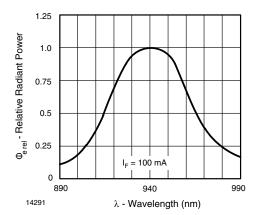


Fig. 8 - Relative Radiant Power vs. Wavelength





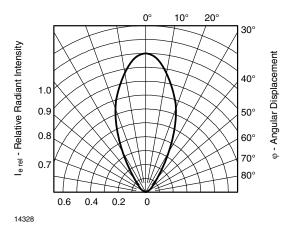
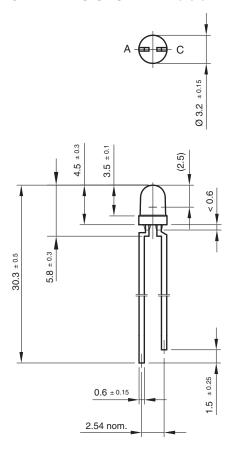


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

#### **PACKAGE DIMENSIONS** in millimeters



Area not plane

Ø 2.9 ± 0.15

technical drawings according to DIN specifications

Drawing-No.: 6.544-5255.01-4

Issue: 7; 25.09.08

95 10913



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